

Title: SUBSTRATE PROCESSING METHOD AND SUBSTRATE PROCESSING APPARATUS

Publication number: JP2002217157 (A)

Publication date: 2002-08-02

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Application number: JP20010009207 20010117

Priority number(s): JP20010009207 20010117

INPADOC patent family: US2002132480 (A1)

Abstract:

PROBLEM TO BE SOLVED: To block a generation of particle contamination by preventing a back-flow from a mist trap to a process chamber when a substrate to be treated is treated feeding a process gas and a solvent vapor.

SOLUTION: This substrate processing apparatus comprises a substrate temperature up process for raising the temperature of a semiconductor wafer W by feeding hot air into the process chamber 10, a substrate treatment process in which the semiconductor wafer W is treated by feeding an ozone gas and a water vapor, a vapor-liquid separation process in which the ambience exhausted from the process chamber 10 during substrate treatment processing is separated into a vapor and a liquid, and a purge process for purging the inside of the process chamber 10 by feeding a purge gas.; During the substrate temperature up process, gating valves V9, V10 arranged on the way of an exhaust pipe 91 from the process chamber 10 to the mist trap 95 are shut down to block the back-flow.

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